

MOS FIELD EFFECT TRANSISTOR 2SK3814

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3814 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

• Super low on-state resistance

 $R_{DS(on)1}$ = 8.7 m Ω MAX. (Vgs = 10 V, ID = 30 A)

 $R_{DS(on)2} = 10.5 \text{ m}\Omega \text{ MAX}. \text{ (Vgs} = 4.5 \text{ V, I}_D = 30 \text{ A)}$

• Low Ciss: Ciss = 5450 pF TYP.

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3814	TO-251 (MP-3)		
2SK3814-Z	TO-252 (MP-3Z)		

(TO-251)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	60	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	±60	Α
Drain Current (pulse) Note1	D(pulse)	±240	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	84	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Energy Note2	Eas	102	mJ
Repetitive Avalanche Current Note3	lar	32	Α
Repetitive Avalanche Energy Note3	Ear	102	mJ

(TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

3. $T_{ch(peak)} \le 150^{\circ}C$, Rg = 25 Ω

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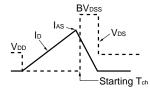
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 60 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y fs	V _{DS} = 10 V, I _D = 30 A	22	44		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 30 A		7.0	8.7	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 30 A		7.9	10.5	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		5450		pF
Output Capacitance	Coss	V _{GS} = 0 V		550		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		350		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30 V, I _D = 30 A		23		ns
Rise Time	tr	V _{GS} = 10 V		8.5		ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		85		ns
Fall Time	tr			7.7		ns
Total Gate Charge	QG	V _{DD} = 48 V		95		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		17		nC
Gate to Drain Charge	Q _{GD}	I _D = 60 A		26		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 60 A, V _{GS} = 0 V		0.95	1.5	V
Reverse Recovery Time	trr	I _F = 60 A, V _{GS} = 0 V		36		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		40		nC

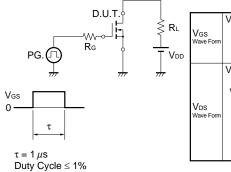
Note Pulsed

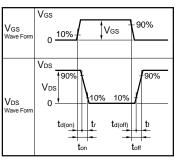
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD} V_{DD} V_{DD} V_{DD}



TEST CIRCUIT 2 SWITCHING TIME



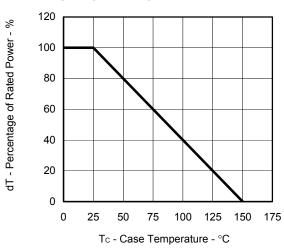


TEST CIRCUIT 3 GATE CHARGE

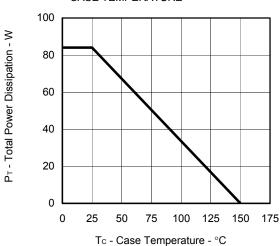
$$\begin{array}{c|c} D.U.T. \\ I_G = 2 \stackrel{m}{\text{M}} \\ \hline \\ PG. \\ \end{array} \begin{array}{c} S \\ 50 \\ \Omega \\ \end{array} \begin{array}{c} RL \\ \hline \\ V_{DD} \\ \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

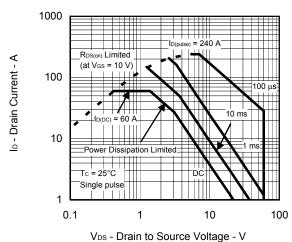
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



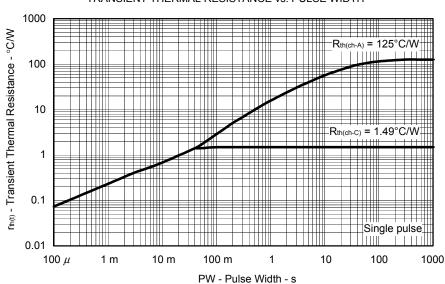
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA



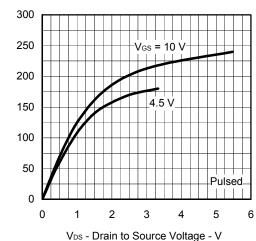
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



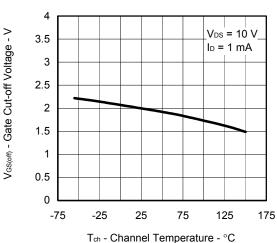
3

lo - Drain Current - A

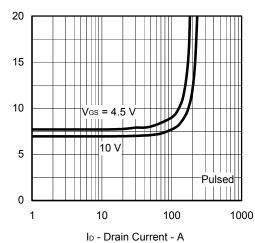
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



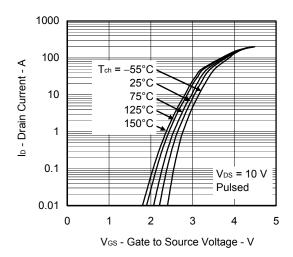
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



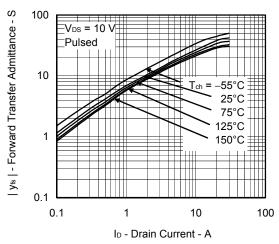
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



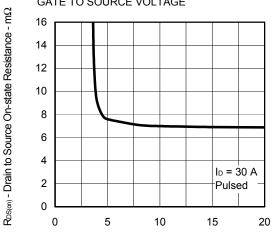
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

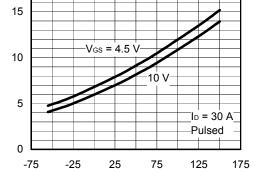


V_{GS} - Gate to Source Voltage - V

R_{DS(m)} - Drain to Source On-state Resistance - mΩ

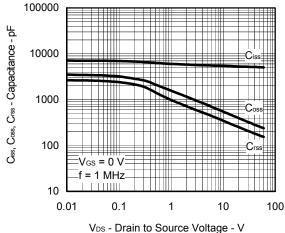
R_{DS(on)} - Drain to Source On-state Resistance - mΩ

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE 20

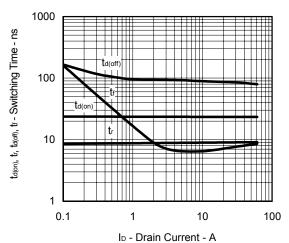


Tch - Channel Temperature - °C

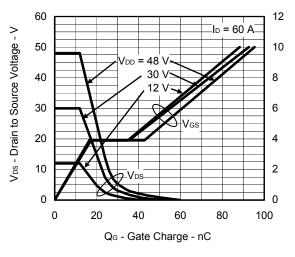
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



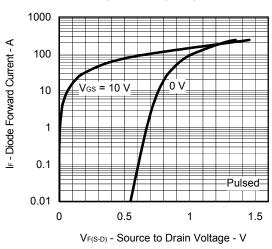
SWITCHING CHARACTERISTICS



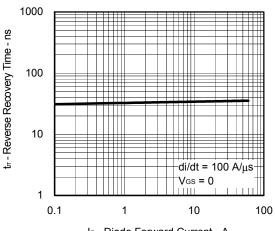
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



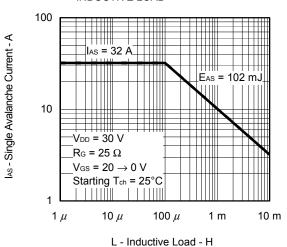
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



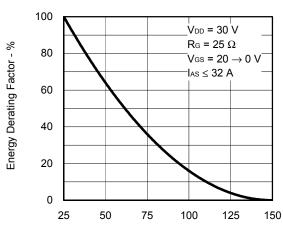
IF - Diode Forward Current - A

Ves - Gate to Source Voltage - V

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



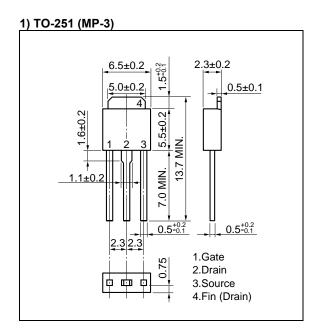
SINGLE AVALANCHE ENERGY DERATING FACTOR

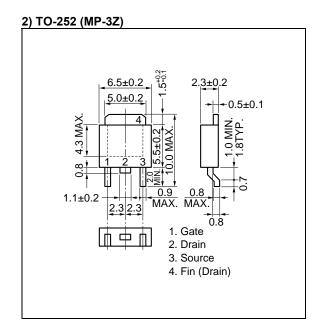


Starting T_{ch} - Starting Channel Temperature - $^{\circ}\text{C}$

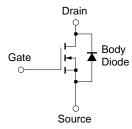


PACKAGE DRAWINGS (Unit: mm)





EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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